

Briefs: Renesas to make LSIs for 3G mobiles

13 February 2006

Chipmaker Renesas Technology will develop a next-generation large-scale integration circuit, a Japanese daily reported Monday.

The Nihon Keizai Shimbun said that the semiconductor manufacturer will collaborate with NTT DoCoMo, Fujitsu, Mitsubishi Electric and Sharp among others to develop LSIs for third-generation phones.

The plan is to have the product ready for use by the autumn of 2007.

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